

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	18359	getter\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:11
2	BRS	L2	345023 5	plug or contact	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:13
3	BRS	L3	310438	dop\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:12
4	BRS	L4	509883	dop\$6 or implant\$6 or inplant\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:12
5	BRS	L5	1610	getter\$6 same dop\$6 same (dop\$6 or implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	136995 14	phosphorous or P or arsenic or ar or antimony or sb or bismuth or bi or boron or B or aluminium or Al or gallium or Ga or indium or In or helium or He or neon or Ne or argon or ar or krypton or kr or xenon or Xe or germanium or Ge	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:13
7	BRS	L8	1218	(getter\$6 same dop\$6 same (dop\$6 or implant\$6 or inplant\$6)) same (phosphorous or P or arsenic or ar or antimony or sb or bismuth or bi or boron or B or aluminium or Al or gallium or Ga or indium or In or helium or He or neon or Ne or argon or ar or krypton or kr or xenon or Xe or germanium or Ge)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:14
8	BRS	L6	52	getter\$6 near8 (plug or contact) near8 (dop\$6 or implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:14
9	BRS	L9	419408 1	plug or contact or groove or trench\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:15
10	BRS	L10	762	1 near4 9	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:15

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	180	10 near8 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:17
12	BRS	L12	151	11 and (@ad<20010403)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 08:18

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	180	(getter\$6 near4 (plug or contact or groove or trench\$3)) near8 (phosphorous or P or arsenic or ar or antimony or sb or bismuth or bi or boron or B or aluminium or Al or gallium or Ga or indium or In or helium or He or neon or Ne or argon or ar or krypton or kr or xenon or Xe or germanium or Ge)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 10:21
2	BRS	L2	151	((getter\$6 near4 (plug or contact or groove or trench\$3)) near8 (phosphorous or P or arsenic or ar or antimony or sb or bismuth or bi or boron or B or aluminium or Al or gallium or Ga or indium or In or helium or He or neon or Ne or argon or ar or krypton or kr or xenon or Xe or germanium or Ge)) and (@ad<20010403)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 11:00
3	BRS	L3	29	1 not 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 10:22
4	BRS	L6	54	getter\$6 near8 (plug or contact or groove or trench\$3) near8 (doped or doping or implant ot implanting)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/04/19 11:03

## Patent Assignment Abstract of Title

### Total Assignments: 1

**Application #:** 09824933

**Filing Dt:** 04/03/2001

**Patent #:** NONE

**Issue Dt:**

**PCT #:** NONE

**Publication #:** NONE

**Pub Dt:**

**Inventor:** Ming-Ren Lin

**Title:** Scribe lane for gettering of contaminants on SOI wafers and gettering method

### Assignment: 1

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**Conveyance:** ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

**Assignor:** LIN, MING-REN

**Exec Dt:** 03/29/2001

**Assignee:** ADVANCED MICRO DEVICES, INC.

P.O. BOX 3453

ONE AMD PLACE

SUNNYVALE, CALIFORNIA 94088

**Correspondent:** RENNER, OTTO ET AL

THOMAS W. ADAMS

1621 EUCLID AVENUE, NINETEENTH FLOOR

CLEVELAND, OH 44115

Search Results as of: 4/19/2004 9:17:32 A.M.